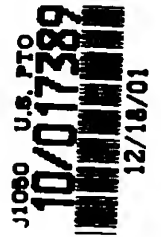


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re New Patent Application of)
Akihiko ISHIBASHI et al.)
Japanese Priority Application 2000-386624) Attn: Applications
Japanese Priority Date: December 20, 2000) Branch
For: METHOD FOR FABRICATING)
SEMICONDUCTOR, METHOD FOR)
FABRICATING SEMICONDUCTOR)
SUBSTRATE, AND SEMICONDUCTOR)
LIGHT EMITTING DEVICE) Date: December 18, 2001



INFORMATION DISCLOSURE STATEMENT

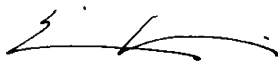
Honorable Commissioner for Patents and Trademarks
Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the reference listed on the attached Form PTO-1449 be made of record in the above-identified application.

A copy of this reference is submitted herewith in accordance with 37 C.F.R. 1.98(a).

Respectfully submitted,


Eric J. Robinson
Registration No. 38,285

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